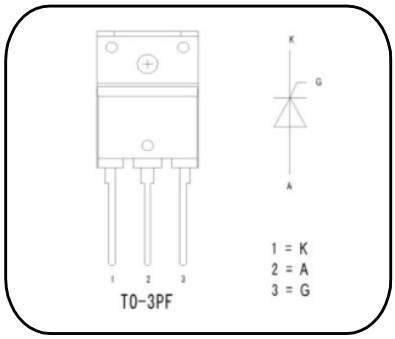


Typical Applications

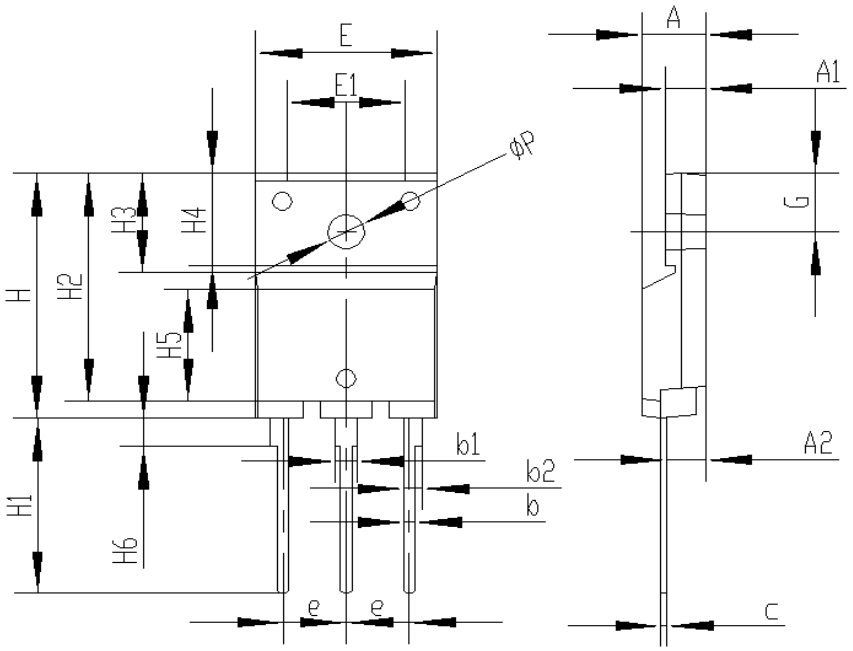
- High power industrical and power transmissior
- DC and AC motor control
- AC controllers

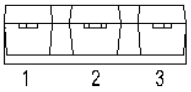
Features

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz	125			60	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V_{DRM}&V_{RRM}, tp=10ms	125			1600	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			10	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			600	A
I^2t	I^2t for fusing coordination					1800	A^2s
V_{TM}	Peak on-state voltage	I_{TM}=60A，tp=380μs	25			1.6	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM}	125			700	V/μs
di/dt	Critical rate of rise of on-state current		125			100	A/μs
I_L	Latching current	I_G=1.2 I_{GT}	25			200	mA
I_{GT}	Gate trigger current	V_A=12V, I_A=1A	25	20		100	mA
V_{GT}	Gate trigger voltage					1.8	V
I_H	Holding current					150	mA
V_{GD}	Non-trigger gate voltage	V_D=12V	125	0.20			V
$R_{th(j-c)}$	Thermal resistance Junction to case				0.8		°C /W
T_j	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		150	°C
Outline	TO-3PF						

Outline:





TO-3PF

	单位: mm		
	MIN	NOM	MAX
A	5.3	5.5	5.7
A1	3.25	3.45	3.65
A2	3.15	3.35	3.55
b	0.85	1.0	1.15
b1	1.85	2.0	2.15
b2	1.45	1.6	1.75
c	0.4	0.5	0.6
e	5.3	5.45	5.6
E	15.40	15.60	15.80
E1	10.00	10.20	10.40
H	22.80	23.00	23.20
H1	16.00	16.50	17.00
H2	21.20	21.40	21.60
H3	9.10	9.30	9.50
H4	8.55	8.75	8.95
H5	10.20	10.40	10.60
H6	2.55	2.70	2.85
G	5.3	5.5	5.7
ØP	3.05	3.2	3.35